Ferrite Magnetic-Anisotropy Field Effects on Inductance and Quality Factor of Planar GHz Inductors

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Abstract—Planar gigahertz (GHz) inductors were fabricated based on high crystalline-anisotropy Zn_{0.13}Co_{0.04}Ni_{0.63}Fe_{2.2}O₄ (Zn-Co-Ni ferrite) and Ba₃Co₂Fe₂₄O₄₁ (Co₂Z hexaferrite) and characterized for inductance (L) and quality (Q) factor. The planar ferrite inductors show an L of 4.5 nH (Zn-Co-Ni), 5.6 nH (Zn-Co-Ni + low H_k and f_{FMR} Co₂Z:), and 4.8 nH (Zn-Co-Ni + high H_k and f_{FMR} Co₂Z:) at 2 GHz. The corresponding L-densities are 18.0, 22.4, and $19.2 \,\mathrm{nH/mm^2}$, which are greater than $16.8 \,\mathrm{nH/mm^2}$ of the air-core inductor. With respect to the Q factor, the air-core and ferrite inductors exhibit Q factors of 6.7 (air-core), 4.8 (Zn-Co-Ni), 2.8 (Zn-Co-Ni + low H_k Co₂Z), and 4.0 (Zn-Co-Ni + high H_k Co₂Z) at 2 GHz. The tan δ_{μ} of the ferrites caused a reduction in the Q factor. Nevertheless, the high H_k and f_{FMR} Co₂Z ferrite inductor demonstrates a higher Q factor than that of the low H_k and f_{FMR} Co₂Z inductor. It is, therefore, suggested that high resistivity, anisotropy, magnetization ferrite can produce large L density and Q factor GHz inductors.

1. INTRODUCTION

Radio frequency (RF) transceivers with fully integrated circuits, including voltage controlled oscillators, low-noise amplifiers, and frequency filters, are in high demand for mobile electronic devices. In response to this, a large number of inductors are integrated into RF integrated circuits (RFICs). However, the inductors consume a large area of the RFICs, and their quality (Q) factors are critical for power management and RF signal processing. Therefore, compact and high Q integrated inductors are required.

Integrated magnetic inductors have been widely investigated. A high-permeability material increases the L and Q factor of inductors by increasing magnetic flux density and decreasing coil resistance and parasitic capacitance [1, 2]. A 2 µm thick CoZrTa magnetic film inductor with relative permeability (μ_r) of about 1000 showed a high L density of $1.3 \,\mu\text{H/mm}^2$ and a 28 times increase in L compared to that of the air-core inductor [2]. However, low resistivity ($\rho = 99 \,\mu\Omega \cdot cm$) of the CoZrTa film decreased the Q factor below 6 at 1 GHz.

In an effort to address the low Q factor, multilayered magnetic films [3–5] or high-resistivity ferrites ($\rho > 1 \,\mathrm{k\Omega \cdot cm}$) [6–9] were used in integrated inductors to suppress GHz eddy current loss. A FeGaB/Al₂O₃ multilayer solenoid inductor showed an L-density of $15 \,\mathrm{nH/mm^2}$ and Q factor of 14 at 1.2 GHz [4]. A Ni_{0.4}Zn_{0.4}Cu_{0.2}Fe₂O₄ (Ni-Zn-Cu) ferrite spiral inductor had an L-density of 12 nH/mm^2 (L of 1.94 nH) and Q factor of 17.2 at 4 GHz, which were increases of about 3.9% and 6.3%, respectively, compared to those of the air-core inductor [9]. It is found that the high-resistivity ferrite is effective in increasing both L and Q factor at GHz frequencies [9, 10]. The L of the ferrite inductor is enhanced by

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Received 9 February 2016, Accepted 10 April 2016, Scheduled 26 April 2016

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the ferrite's magnetic permeability ($\mu_r > 1$). The magnetic loss tangent (tan δ_{μ}) of the ferrite plays a role and causes a decrease in GHz Q factor.

The Q factor of the ferrite inductor can be expressed by the air-core and magnetic-core components in Eq. (1) [13],

$$Q = \frac{\omega L}{R} = \frac{\omega L}{(R_{\rm AC} + \Delta R)}.$$
(1)

The resistance $(R_{\rm AC})$ of the air-core inductor is mainly attributed to conductor loss from skin-depth effect. The magnetic-core loss $(\Delta R \propto \tan \delta_{\mu})$ is related to the frequency-dependent loss $\tan \delta_{\mu}$. The $\tan \delta_{\mu}$ increases with frequency and becomes considerably large when the operating frequency approaches the ferromagnetic resonance frequency (f_{FMR}) of the ferrite. Therefore, a high f_{FMR} ferrite is required, thereby contributing to low-loss characteristics and realizing high $Q \,\mathrm{GHz}$ inductors. According to Eq. (2) [11]

$$f_{FMR} = (\gamma/2\pi) \sqrt{(4\pi M_s H_k)},\tag{2}$$

 f_{FMR} increases with increasing H_k , where H_k is the magneto-crystalline anisotropy field, M_s the saturation magnetization, and $\gamma/2\pi$ the gyromagnetic constant (2.8 MHz/Oe). In contrast, ferrite's μ_r decreases with increasing f_{FMR} by the Snoek law in Eq. (3) [12]

$$(\mu_r - 1) \cdot f_{FMR} = \frac{4}{3} \gamma M_s, \tag{3}$$

and L consequently decreases. Therefore, a high crystalline-anisotropy ferrite inductor needs to be

designed in consideration of magnetic parameters, including H_k , M_s , μ_r , f_{FMR} , and $\tan \delta_{\mu}$. In this paper, we investigate the relation of H_k to inductor Q factor and report electrical characteristics of high crystalline-anisotropy Zn_{0.13}Co_{0.04}Ni_{0.63}Fe_{2.2}O₄ (Zn-Co-Ni ferrite) and $Ba_3Co_2Fe_{24}O_{41}$ (Co_2Z hexaferrite) inductors in comparison to an air-core inductor.

2. FUNDAMENTALS OF FERRITE INDUCTOR

2.1. Inductance and Quality Factor of a Ferrite Inductor

The L of the ferrite inductor can be given by the sum of the air-core inductance (L_{AC}) and the inductance gain (ΔL) from the high-permeability ferrite in Eq. (4) [13],

$$L = L_{\rm AC} + \Delta L. \tag{4}$$

 $L_{\rm AC}$ depends primarily on the geometry of a coil structure, including the length, width, and thickness. On the other hand, the gain ΔL is proportional to magnetic properties and geometry parameters of the ferrite in Eq. (5) [14, 15],

$$\Delta L \approx \mu_0 \mu_{eff} \frac{t_m w_m}{2l_m},\tag{5}$$

where

$$\mu_{eff} = \frac{\mu_r}{1 + N_d(\mu_r - 1)},$$

 t_m , w_m , and l_m are the thickness, width, and length of the ferrite, and N_d is the demagnetization factor. Accordingly, the L of the ferrite inductor can be enhanced by the ferrite's magnetic permeability ($\mu_r > 1$) as compared to the air-core $(\mu_r = 1)$ inductor.

The Q factor of the ferrite inductor is a function of the alternating current (AC) conductor loss $(R_{\rm AC})$ and magnetic-core loss $(\Delta R \propto \tan \delta_{\mu})$ according to Eq. (1). The $R_{\rm AC}$ can be reduced by the design optimization of inductor coil thickness, width, and length. With respect to the magnetic-core loss, the loss $\tan \delta_{\mu}$ is expressed by three main contributions in Eq. (6) [16],

$$\tan \delta_{\mu} = \tan \delta_h + \tan \delta_e + \tan \delta_r, \tag{6}$$

where $\tan \delta_h$ is the hysteresis loss, $\tan \delta_e$ the eddy current loss, and $\tan \delta_r$ the residual loss. For highresistivity, soft-magnetic ferrites, the $\tan \delta_h$ and $\tan \delta_e$ become neligible. However, the $\tan \delta_r$, which is determined by the domain wall and spin rotational resonances, is predominant [17, 18]. For high Q ferrite inductors, the tan δ_{μ} associated with the residual loss needs to be minimized.

2.2. Permeability Dispersion and Magnetic Loss of Ferrite

Permeability dispersion of a polycrystalline ferrite is associated with the domain wall motion and spin rotation, as given by Eqs. (7) and (8) [19]

$$\mu' = 1 + \frac{K_{DW}\omega_{DW}^2 \left(\omega_{DW}^2 - \omega^2\right)}{\left(\omega_{DW}^2 - \omega^2\right)^2 + \beta^2 \omega^2} + \frac{K_{sp}\omega_{sp}^2}{\omega_{sp}^2 + \omega^2},\tag{7}$$

$$\mu'' = \frac{K_{DW}\omega_{DW}^2\beta\omega}{\left(\omega_{DW}^2 - \omega^2\right)^2 + \beta^2\omega^2} + \frac{K_{sp}\omega\omega_{sp}}{\omega_{sp}^2 + \omega^2},\tag{8}$$

where K_{DW} is the static magnetic susceptibility, $\omega_{DW} (= 2\pi f_{DW})$ the resonance frequency, β the damping factor of the domain wall motion, K_{sp} the static magnetic susceptibility, and $\omega_{sp} (= 2\pi f_{sp})$ the resonance frequency of the spin rotation. Based on the above equations, the individual loss components (i.e., $\tan \delta_{DW}$ and $\tan \delta_{sp}$) of the ferrite can be obtained by Eqs. (9) and (10), respectively.

$$\tan \delta_{DW} = \left(\frac{K_{DW}\omega_{DW}^2\beta\omega}{\left(\omega_{DW}^2 - \omega^2\right)^2 + \beta^2\omega^2}\right) \left/ \left(\frac{K_{DW}\omega_{DW}^2\left(\omega_{DW}^2 - \omega^2\right)}{\left(\omega_{DW}^2 - \omega^2\right)^2 + \beta^2\omega^2}\right) = \frac{\beta\omega}{\omega_{DW}^2 - \omega^2}.$$
(9)

$$\tan \delta_{sp} = \left(\frac{K_{sp}\omega\omega_{sp}}{\omega_{sp}^2 + \omega^2}\right) / \left(\frac{K_{sp}\omega_{sp}^2}{\omega_{sp}^2 + \omega^2}\right) = \frac{\omega}{\omega_{sp}}.$$
(10)

It is noted that both the loss $\tan \delta_{DW}$ and $\tan \delta_{sp}$ decrease with increasing the resonance frequencies, ω_{DW} and ω_{sp} . It is known that the domain wall resonance contributes to low-frequency permeability dispersion, while the spin rotational resonance is dominant in high-frequency permeability dispersion [20]. The high-frequency resonance frequency of ferrite, which is referred to as f_{FMR} , can be increased with high H_k according to Eq. (2). Therefore, high resistivity, crystalline-anisotropy ferrite is necessary for high *L*-density and *Q*-factor GHz inductors.

3. EXPERIMENT

3.1. Inductor Design and Fabrication

A one-turn spiral inductor was designed as shown in Fig. 1(a). The inductor has a coil area of $0.5 \times 0.5 \text{ mm}^2$, width of $15 \,\mu\text{m}$, space of $50 \,\mu\text{m}$, and thickness of $7 \,\mu\text{m}$. A bonding wire was used between the center and outermost pads for an electrical connection. This designed coil structure was



Figure 1. (a) Designed one-turn spiral inductor and (b) optical microscope image of the fabricated air-core inductor.





Figure 2. Photo-images of (a) embedded-type Co_2Z hexaferrite inductor (bottom Zn-Co-Ni ferrite film + top Co_2Z ferrite particles), (b) bottom-type Zn-Co-Ni ferrite film inductor, and (c) short and (d) open de-embedding structures.

used in simulating inductor performance (using ANSYS HFSS ver. 11) and fabricating air-core and ferrite inductors.

Figure 1(b) shows the air-core inductor that was fabricated on a 0.6 μ m thick silicon oxide (SiO₂)/600 μ m thick Si substrate. The conductivity (σ) of the Si substrate is 10–100 S/m. Figs. 2(a) and (b) exhibit the fabricated ferrite inductors with two different structures. One is the embedded-type ferrite inductor, where the inductor coil is positioned between the bottom Zn-Co-Ni ferrite film and top Co₂Z hexaferrite particles as shown in Fig. 2(a). The second is the bottom-type ferrite inductor, having the coil formed on the Zn-Co-Ni ferrite film as presented in Fig. 2(b).

To fabricate the inductors, a microfabrication process and sputtering deposition were employed. First, a 2.45 μ m thick Zn-Co-Ni ferrite film was deposited on the SiO₂/Si substrate, followed by Au (50 nm)/Ti (20 nm) seed layers for use in copper (Cu) coil electroplating. A 10 μ m thick photoresist (PR) mold (Microchem KMPR1005) was then photolithographically produced on the Au/Ti layers. A 7 μ m thick Cu coil was subsequently deposited by electroplating, followed by PR stripping and ion beam etching (IBE) of the Au/Ti layers for the bottom-type ferrite inductor as shown in Fig. 2(b). A mixture of Co₂Z hexaferrite particles and ethanol was applied on the top of the bottom-type ferrite inductor as presented in Fig. 2(a).

3.2. Preparation of High Crystalline-Anisotropy Zn-Co-Ni Ferrite Film and Co_2Z Hexaferrite Particles

The Zn-Co-Ni ferrite film was prepared by the sequential direct current (DC) magnetron sputtering of nickel (Ni), iron (Fe), zinc (Zn), and cobalt (Co) metal targets in a mixture of 75% Ar and 25% O₂. During the sputtering deposition, the substrate temperature was held at 850°C, and the working pressure and DC power for each target were 5 mTorr and 250 W (200 W for Zn), respectively. The deposited multilayered oxide films were post-annealed at 850°C for 4 hours in a mixture of 67% Ar and 33% O₂ in order to crystallize the films into the Zn-Co-Ni ferrite.

With regard to Co_2Z hexaferrite particles, the solid-state reaction process was used. The detailed process is reported elsewhere [21, 22]. Two different-sized Co_2Z particles were prepared with and without 10-hour ball milling for the embedded-type ferrite inductor.

3.3. Measurement

The static magnetic properties and crystalline phases of the Zn-Co-Ni ferrite film and Co_2Z particles were characterized by a vibrating sample magnetometer (MicroSense EV9) and X-ray diffractometer, respectively. A scanning electron microscope (SEM: JEOL 7000) was used to observe the cross-sectional image of the Zn-Co-Ni ferrite film.

To measure inductor electrical characteristics, a vector network analyzer (Agilent N5260A) and GSG probes (Cascade Microtech ACP40-GSG-200) were used. The L and Q factor of the air-core and ferrite inductors were calculated from the measured complex two-port scattering (S)-parameters (S_{11} , S_{12} , S_{21} , and S_{22}) [23]. The experimental setup for the inductor measurement is shown in Fig. 2(a). The probes were calibrated using the short-open-load-through (SOLT) technique with an impedance standard substrate (Cascade Microtech 101-190). The de-embedding technique [24] was also used to eliminate the parasitic effects of the probe pads and ground structure. The short and open de-embedding structures are shown in Figs. 2(c) and (d), respectively.

4. RESULTS AND DISCUSSION

4.1. Properties of High Crystalline-Anisotropy Zn-Co-Ni Ferrite Film and Co₂Z Hexaferrite Particles

The measured X-ray diffraction patterns confirm that the Zn-Co-Ni ferrite film (in Fig. 3) and Co_2Z particles (not shown here) are well crystallized into spinel and hexagonal ferrites, respectively. The cross-sectional SEM image in Fig. 4 shows that the Zn-Co-Ni ferrite film has a thickness of 2.45 µm and a smooth and clean surface.



2.45 μm thick Zn-Co-Ni ferrite Silicon wafer

Figure 3. X-ray diffraction pattern of the fabricated Zn-Co-Ni ferrite film on silicon substrate.

Figure 4. Scanning electron microscope (SEM) cross-sectional image of the Zn-Co-Ni ferrite film.

Figure 5 shows the measured magnetic hysteresis loop of the Zn-Co-Ni ferrite film. The saturation magnetization (M_s) and coercivity (H_c) of the film are 334 emu/cm³ and 178 Oe, respectively. The in-plane H_k of the ferrite film is 420 Oe, which was obtained by the method in [25]. It is noted that the fabricated Zn-Co-Ni ferrite film has higher M_s and H_k than those of low crystalline-anisotropy Ni-Zn-Cu $(M_s = 204 \text{ emu/cm}^3, H_k = 401 \text{ Oe})$ and YIG $(M_s = 94 \text{ emu/cm}^3, H_k = 238 \text{ Oe})$ ferrites [9]. It is, therefore, expected that the f_{FMR} of the Zn-Co-Ni ferrite film increases with high M_s and H_k according to the relation $f_{FMR} = (\gamma/2\pi)(4\pi M_s H_k)^{0.5}$.

The measured magnetic hysteresis loops for the two different-sized Co₂Z hexaferrites are presented in Fig. 6. One is the non-milled Co₂Z, while the other is the 10-hour milled Co₂Z particles. The 10-hour milled Co₂Z particles exhibit saturation magnetization (σ_s) of 49 emu/g and H_c of 168 Oe. On the other



Figure 5. Measured magnetic hysteresis loop of the Zn-Co-Ni ferrite film.



Figure 6. Measured magnetic hysteresis loops of the non-milled and 10-hour milled Co_2Z hexaferrite particles.

hand, the non-milled Co₂Z particles show σ_s of 50 emu/g and H_c of 23 Oe. The larger H_c of the milled Co₂Z implies a higher H_k than that of the non-milled Co₂Z [21].

With respect to dynamic magnetic properties, we calculated the frequency-dependent complex permeability for the Zn-Co-Ni ferrite film using Eq. (11) and permeability spectra for the Co₂Z hexaferrite particles in order to estimate μ_r , tan δ_{μ} , and f_{FMR} . The complex permeability of the ferrite film can be calculated by Eq. (11) [26],

$$\mu(\omega) = 1 + \frac{\gamma 4\pi M_s}{\gamma H_k + j\alpha\omega} \times \left[1 + \frac{\omega^2}{(\gamma H_k + \gamma 4\pi M_s + j\alpha\omega)(\gamma H_k + j\alpha\omega) - \omega^2}\right],\tag{11}$$

where ω is the angular driving frequency, γ the gyromagnetic constant (1.76 × 10⁷ rad/Oe·s), and α the damping constant. Thus, the parameters in the calculation include the experimental M_s of 334 emu/cm³, in-plane H_k of 420 Oe, and α of 0.05 [27]. The calculated complex permeability spectra are presented in Fig. 7. The real part of permeability (μ') is about 14 at 2 GHz. The loss tan δ_{μ} (at 2 GHz) and f_{FMR} are 0.11 and 3.86 GHz, respectively. The f_{FMR} is determined by the maximum imaginary part of permeability (μ''). It is noted that the large H_k and M_s of the Zn-Co-Ni ferrite film leads to a higher



Figure 7. Calculated complex permeability of the Zn-Co-Ni ferrite film using the parameters $M_s = 334 \text{ emu/cm}^3$, $H_k = 420 \text{ Oe}$, and $\alpha = 0.05$.



Figure 8. Measured complex permeability of the non-milled and 10-hour milled Co_2Z hexaferrites.

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 f_{FMR} than 0.26 GHz of the Ni-Zn-Cu ferrite and 0.06 GHz of the YIG [9]. The μ' and $\tan \delta_{\mu}$ were used in inductor performance simulation.

To measure the frequency-dependent complex permeability of the Co₂Z hexaferrite, the Co₂Z particles were formed into a toroidal ring (inner diameter: 3.2 mm, outer diameter: 7.8 mm) and characterized with an impedance/material analyzer (Agilent E4991). Fig. 8 presents the measured permeability spectra of the non-milled and 10-hour milled Co₂Z hexaferrites. The μ' at 2 GHz is 3.4 (4.3 at 1 GHz) for the non-milled Co₂Z and 2.1 (2.0 at 1 GHz) for the milled Co₂Z. The corresponding loss tan δ_{μ} are 0.64 (0.3 at 1 GHz) and 0.14 (0.06 at 1 GHz), respectively. It is obvious that the increased H_k of the milled Co₂Z leads to an increase in f_{FMR} (beyond the measured frequency range in Fig. 8) and contributes to an improvement in GHz magnetic loss characteristics.

4.2. Electrical Characteristics of High Crystalline-anisotropy Zn-Co-Ni Ferrite Film Inductor

The fabricated ferrite inductors were characterized for L and Q factor in comparison to those of the air-core inductor. Figs. 9(a) and (b) show the measured and simulated L and Q factor of the bottom-type Zn-Co-Ni ferrite film and air-core inductors. The experimental L and Q factor of the inductors are in close agreement with the simulation results. It is noted that the discontinuity in the measured Q factor in Fig. 9(b) is due to a minor measurement error. The measured L of the Zn-Co-Ni ferrite and air-core inductors are 4.5 and 4.2 nH at 2 GHz, respectively. The corresponding L densities are 18.0 and 16.8 nH/mm². It is found that the Zn-Co-Ni ferrite inductor shows a 7.1% increase in L compared to that of the air-core inductor. The high crystalline-anisotropy Zn-Co-Ni ferrite inductor exhibits a small L increase due to relatively low μ_r .

With respect to the Q factor of the inductors, the Zn-Co-Ni ferrite inductor shows a Q factor of 4.8 at 2 GHz (8.5 at 1 GHz), which is lower than 6.7 (12.5 at 1 GHz) of the air-core inductor. The maximum Q factors are 12.3 at 0.5 GHz for the Zn-Co-Ni ferrite and 14.1 at 0.55 GHz for the air-core inductors. The relatively low Q factor of the ferrite inductor is mainly attributed to $\tan \delta_{\mu}$ of the Zn-Co-Ni ferrite. The measured inductor characteristics, therefore, indicate that GHz magnetic loss of the ferrite plays a critical role in inductor Q factor. It is also found that the low Q factors of both the air-core and Zn-Co-Ni ferrite inductors were caused by the large substrate loss of the high-conductivity Si substrate ($\sigma = 10-100$ S/m). However, when we used the low-conductivity Si substrate ($\sigma = 0.01$ S/m) in inductor performance simulation, the Q factors of the Zn-Co-Ni ferrite and air-core inductors significantly increased to 20.0 and 31.9 at 2 GHz, respectively. The simulation results suggest that the Zn-Co-Ni ferrite film with high M_s of 334 emu/cm³ and H_k of 420 Oe can produce an improved L-density, Q-factor inductor as compared to the low anisotropy Ni-Zn-Cu ferrite and YIG inductors [9].



Figure 9. Measured and simulated (a) L and (b) Q factor of the air-core and Zn-Co-Ni ferrite film inductors.



Figure 10. Measured (a) L and (b) Q factor of the air-core, Zn-Co-Ni ferrite (bottom), Zn-Co-Ni ferrite (bottom) + non-milled Co₂Z hexaferrite (top), and Zn-Co-Ni ferrite (bottom) + 10-hour milled Co₂Z hexaferrite (top) inductors.

Table 1. Measured electrical characteristics of the fabricated air-core and ferrite inductors at 2 GHz.

At $2\mathrm{GHz}$	L (nH)	L increase (%)	Q	Max. Q
Air-core	4.2	-	6.7	$14.1~{\rm at}~0.55{\rm GHz}$
Zn-Co-Ni ferrite film (bottom)	4.5	7.1	4.8	$12.3~{\rm at}~0.50{\rm GHz}$
Zn-Co-Ni ferrite film (bottom) + non-milled Co ₂ Z (low H_k and f_{FMR})	5.6	33.3	2.8	$12.6~{\rm at}~0.35{\rm GHz}$
Zn-Co-Ni ferrite film (bottom) + 10 h-milled Co ₂ Z (high H_k and f_{FMR})	4.8	14.3	4.0	11.7 at $0.43\mathrm{GHz}$

4.3. Effect of Dynamic Magnetic Properties of Co_2Z Hexaferrites on L and Q Factor

To further investigate the effect of dynamic magnetic properties on a ferrite inductor's L and Q factor, two-different sized $C_{02}Z$ hexaferrites were applied to the bottom-type ferrite inductor as shown in Fig. 2(a). Fig. 10 shows the measured L and Q factor of the embedded-type ferrite inductors, with the coil positioned between the bottom Zn-Co-Ni ferrite film and top Co_2Z hexaferrite particles, in comparison to the electrical characteristics of the air-core and bottom-type Zn-Co-Ni ferrite inductors. The embedded-type ferrite inductors show an L of 5.6 nH (Zn-Co-Ni + non-milled Co₂Z: low H_k and f_{FMR}) and 4.8 nH (Zn-Co-Ni + 10-hour milled Co₂Z: high H_k and f_{FMR}) at 2 GHz. These inductances are greater than 4.2 nH of the air-core and 4.5 nH of the Zn-Co-Ni ferrite film inductors. The L of the embedded-type ferrite inductors increase by 33% and 14% compared to the L of the air-core inductor. The corresponding L-densities are 22.4 nH/mm^2 for the low $H_k \text{ Co}_2 \text{Z}$ and 19.2 nH/mm^2 for the high H_k Co₂Z. The significant increase in L occurs because the Co₂Z hexaferrite enhances magnetic flux density and also reduces leakage magnetic flux. On the other hand, the additional $\tan \delta_{\mu}$ from the Co₂Z caused a reduction in the Q factor as shown in Fig. 10(b). It is found that the high H_k and f_{FMR} Co₂Z embedded-type inductor demonstrates a higher Q factor of 4.0 at 2 GHz (7.2 at 1 GHz) than 2.8 (5.3) at 1 GHz) of the low H_k and f_{FMR} Co₂Z inductor. Table 1 summarizes the measured characteristics of the fabricated air-core and ferrite inductors.

4.4. Relation of Magneto-Crystalline Anisotropy Field, H_k to Inductor Q Factor

The experimental inductor characteristics demonstrate that GH tan δ_{μ} plays a role in the inductor Q factor, and therefore, the H_k becomes a key magnetic parameter. Inductor performance simulation was

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carried out to investigate the relation of H_k to inductor Q factor. Fig. 11 shows the dependence of both f_{FMR} and Q factor on H_k at μ_{dc} of 10, 20, and 30. The relation $\mu_{dc} = 1 + 4\pi M_s/H_k$ and the Eqs. (2) and (11) were used to obtain the f_{FMR} (in Fig. 11) and frequency-dependent μ' and $\tan \delta_{\mu}$. The calculated μ' and $\tan \delta_{\mu}$ at 2 GHz were then applied in the inductor simulation to determine the Q factor. The designed inductor geometry shown in Fig. 1(a) was used. The Si-substrate had σ of 0.01 S/m, and the ferrite film had a thickness of 2.45 μ m. As shown in Fig. 11, the f_{FMR} increases with increasing the H_k . At μ_{dc} of 10, the f_{FMR} increases to 5 GHz from less than 2 GHz as the H_k increases from 200 to 600 Oe. The results suggest that the GHz $\tan \delta_{\mu}$ can decrease with high H_k according to Section 2. The corresponding inductor Q factor at 2 GHz is 37.9 with the H_k of 600 Oe and 3.4 with the H_k of 200 Oe. When the H_k is higher than 400 Oe, the ferrite inductors' Q factors become greater than that of the air-core inductor (Q of 31.9 for the Si σ of 0.01 S/m). With respect to the L, the simulated L was about 4.4 nH at μ_{dc} of 10, 4.6 nH at μ_{dc} of 20, and 4.8 nH at μ_{dc} of 30. It is, therefore, suggested that the high H_k and f_{FMR} ferrite inductor with a large M_s is desired for high L density and Q factor GHz inductors.



Figure 11. Calculated f_{FMR} and simulated inductor Q factor at 2 GHz as a function of H_k at μ_{dc} of 10, 20, and 30.

Exploring material candidates suggests that exchange-coupled magnets can meet the desired magnetic properties. The coupling of magnetically soft (i.e., high M_s and small H_k) and hard (i.e., small M_s and high H_k) phases in the exchange-coupled system realizes simultaneously high M_s and large H_k . Therefore, future research will focus on exchange-coupled magnetic GHz inductors.

5. CONCLUSION

Planar GHz inductors were fabricated based on high crystalline-anisotropy Zn-Co-Ni ferrite and Co₂Z hexaferrite and characterized for L and Q factor. The ferrite inductors show L densities of 18.0 nH/mm² (Zn-Co-Ni), 22.4 nH/mm² (Zn-Co-Ni + low H_k and f_{FMR} Co₂Z:), and 19.2 nH/mm² (Zn-Co-Ni + high H_k and f_{FMR} Co₂Z:). With respect to the Q factor, the ferrite inductors exhibit Q factors of 4.8 (Zn-Co-Ni), 2.8 (Zn-Co-Ni + low H_k Co₂Z), and 4.0 (Zn-Co-Ni + high H_k Co₂Z) at 2 GHz. The L densities and Q factors of the ferrite inductors are greater and lower than 16.8 nH/mm² and 6.7 of the air-core inductor, respectively. The high H_k of Zn-Co-Ni ferrite film and Co₂Z hexaferrite results in increased f_{FMR} and moderate μ_r , but the ferrites' tan δ_{μ} causes a decrease in the Q factor. Accordingly, L densities and Q factors are trade-off for GHz ferrites. In addition, low-temperature fabrication technique is inevitable since the ferrite process temperature is incompatible with complementary metal-oxide-semiconductor (CMOS) processing temperature in contrast to air-core inductors. In conclusion, the simulation and experiment results suggest that high resistivity, crystalline-anisotropy, low loss ferrite along with high Q inductor design can give rise to high L density and Q factor GHz inductors.

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